

KJC70R650CF

Super-Junction Power MOSFET

1. Product Information

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Fast Switching Capability
- Lead Free Product is Acquired

Pin Description

Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

Applications

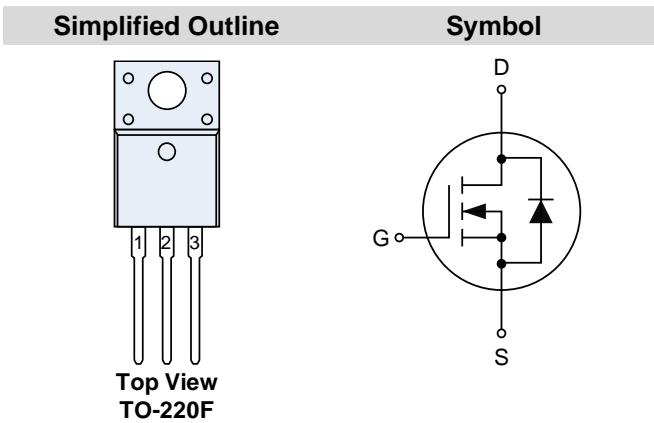
- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Quick reference

$V_{DS} \geq 700$ V

$I_D \leq 7$ A

$R_{DS(ON)} \leq 650$ mΩ @ $V_{GS} = 10$ V (Type: 560 mΩ)



Package Marking and Ordering Information

Product Name	Marking	Package	Packaging	Quantity (pcs)
KJC70R650CF	KJC70R650CF	TO-220F	Tube	50

2. Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	700	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Continuous Drain Current (T _c =25°C)	7	A
	Continuous Drain Current (T _c =100°C)	5.6	A
I_{DM}	Pulsed Drain Current ^[1]	28	A
E_{AS}	Single Pulsed Avalanche Energy ^[2]	120	mJ
I_{AR}	Avalanche Current ^[1]	1.2	A
P_D	Power Dissipation ^[2]	31.25	W
	Power Dissipation, Derate above 25°C ^[2]	0.25	W/°C
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
$R_{θJA}$	Thermal Resistance, Junction-Ambient	68	°C/W
$R_{θJC}$	Thermal Resistance, Junction-Case	4	°C/W

3. Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0 \text{ V}, I_{\text{D}}=250 \mu\text{A}$	700	-	-	V
$I_{\text{DS}(\text{SS})}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=700 \text{ V}, V_{\text{GS}}=0 \text{ V}$	-	-	1	μA
		$V_{\text{DS}}=560 \text{ V}, T_C=125^\circ\text{C}$	-	10	-	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 30 \text{ V}, V_{\text{DS}}=0 \text{ V}$	-	-	± 100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250 \mu\text{A}$	2.5	-	4.0	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance	$V_{\text{GS}}=10 \text{ V}, I_{\text{D}}=3.5 \text{ A}$	-	560	650	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=100 \text{ V}, V_{\text{GS}}=0 \text{ V}, f=1 \text{ MHz}$	-	498	-	pF
C_{oss}	Output Capacitance		-	23	-	pF
C_{rss}	Reverse Transfer Capacitance		-	1.6	-	pF
Switching Characteristics						
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DS}}=400 \text{ V}, I_{\text{D}}=3.5 \text{ A}, V_{\text{GS}}=10 \text{ V}, R_{\text{G}}=25 \Omega$	-	12	-	ns
t_r	Turn-on Rise Time		-	22	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	50	-	ns
t_f	Turn-off Fall Time		-	37	-	ns
Q_g	Total Gate Charge	$V_{\text{DS}}=560 \text{ V}, I_{\text{D}}=3.5 \text{ A}, V_{\text{GS}}=10 \text{ V}$	-	13	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain Charge		-	5	-	nC
Source-Drain Diode Characteristics						
V_{SD}	Drain-Source Diode Forward Voltage	$V_{\text{GS}}=0 \text{ V}, I_{\text{F}}=3.5 \text{ A}$	-	0.85	-	V
I_s	Diode Continuous Forward Current		-	-	7	A
I_{SM}	Maximum Pulsed Body-Diode Forward Current		-	-	28	A
T_{rr}	Reverse Recovery Time	$V_{\text{R}}=400 \text{ V}, I_{\text{F}}=3.5 \text{ A}, \frac{di}{dt}=100 \text{ A}/\mu\text{s}$	-	200	-	ns
Q_{rr}	Reverse Recovery Charge		-	1.3	-	μC

Notes:

- Limited by maximum junction temperature, maximum duty cycle is 0.75.
- $T_J=25^\circ\text{C}$, $V_{\text{DD}}=50 \text{ V}$, $V_{\text{G}}=10 \text{ V}$, $L=0.3 \text{ mH}$, $R_{\text{G}}=25 \Omega$.

4. Test Circuits and Waveforms ($T_J=25^{\circ}\text{C}$)

Table 1. Gate Charge Test Circuit and Waveforms

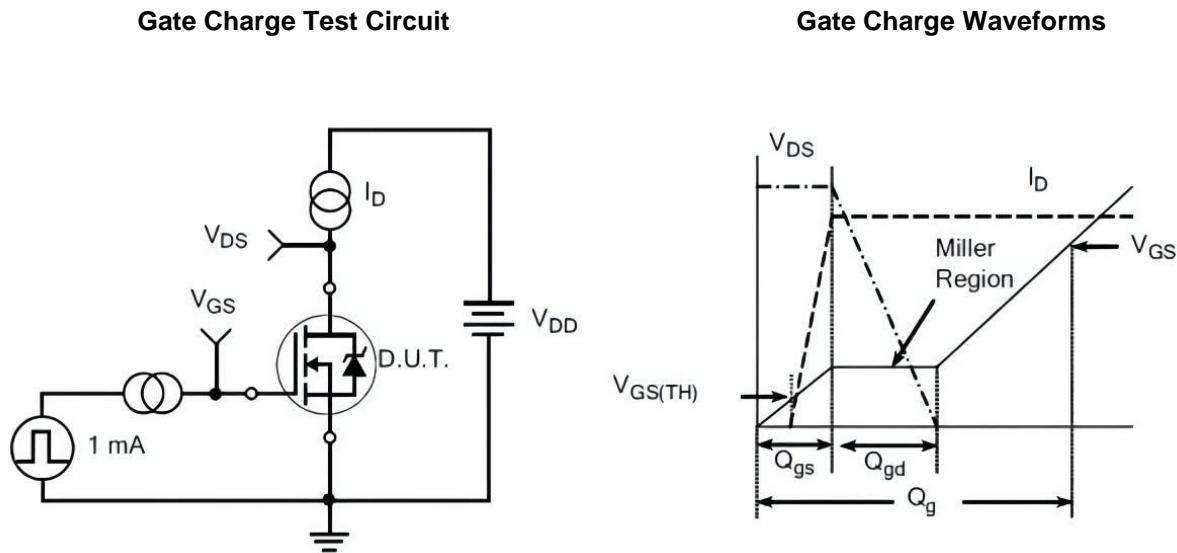


Table 2. Resistive Switching Test Circuit and Waveforms

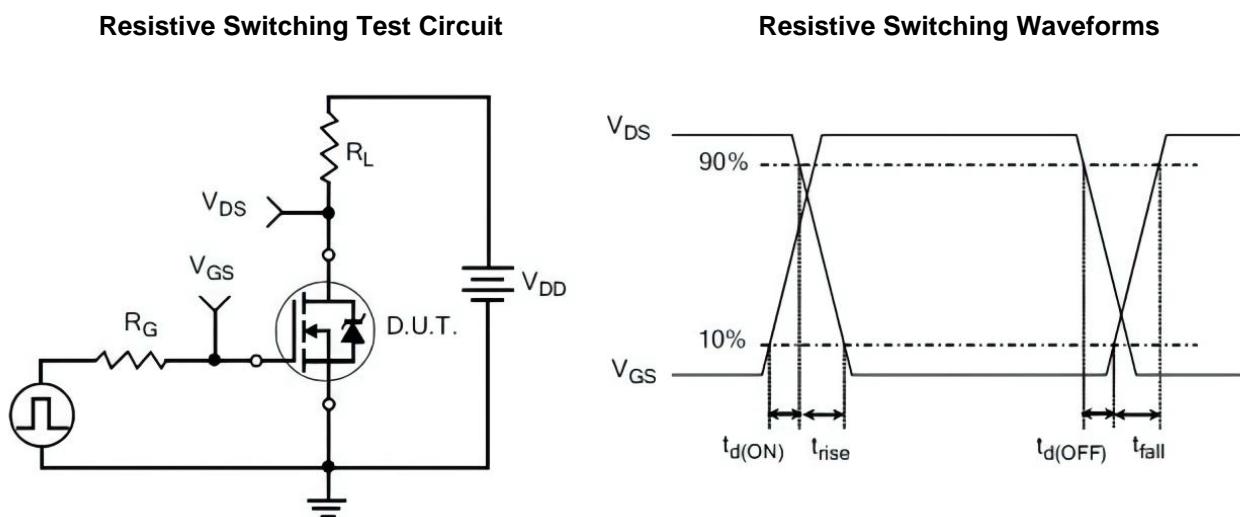


Table 3. Diode Recovery Test Circuit and Waveforms

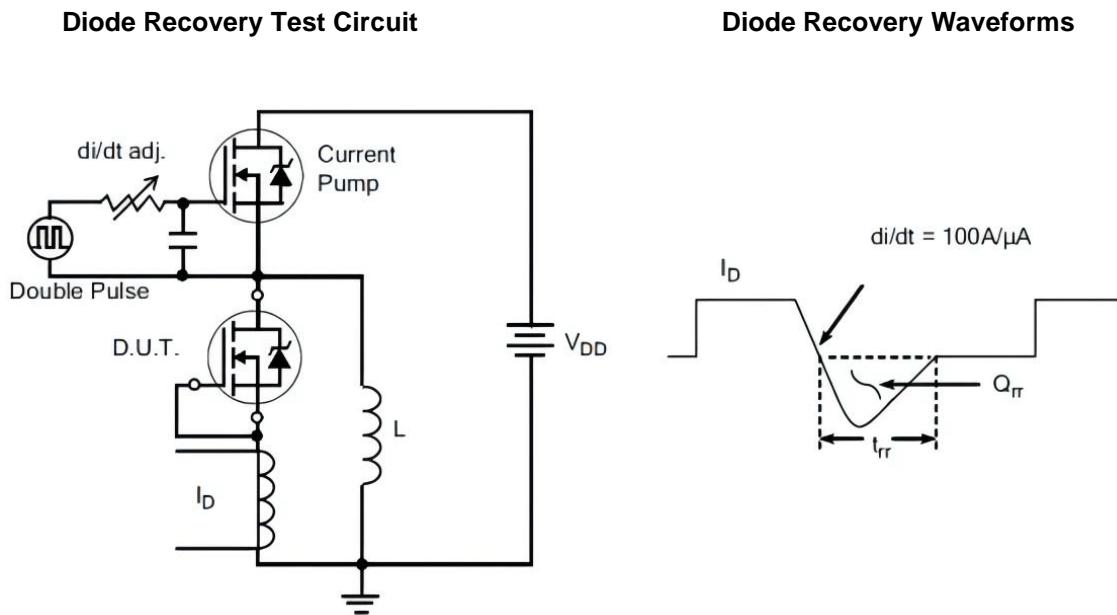
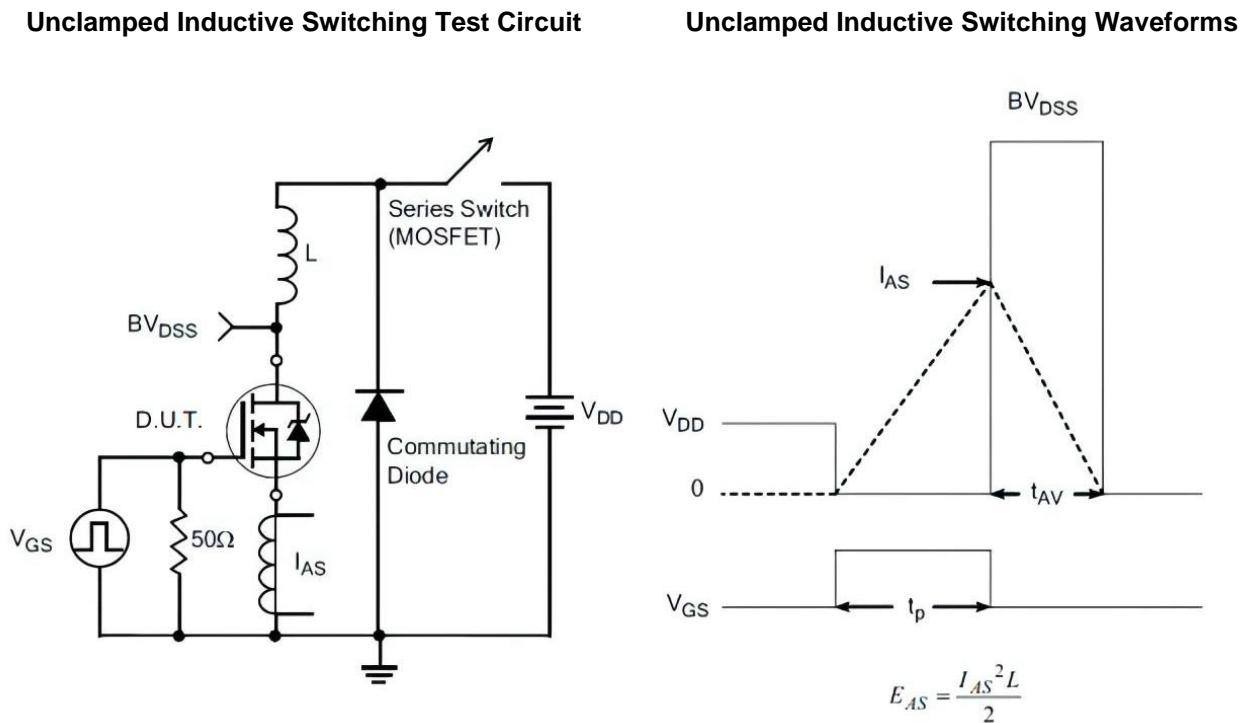


Table 4. Unclamped inductive Switching (UIS) Test Circuit and Waveforms



5. Electrical Characteristics

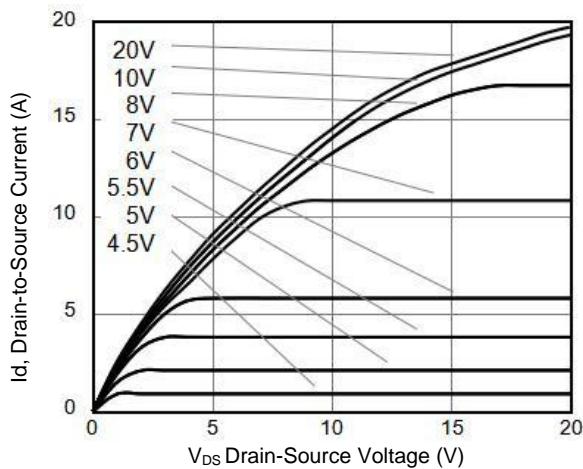


Figure 1. Typical Output Characteristics

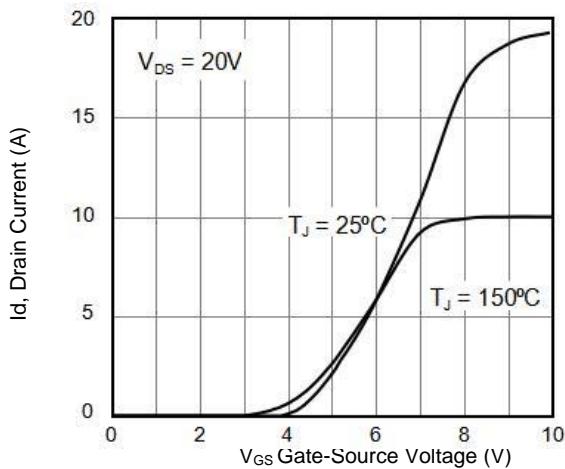


Figure 2. Typical Transfer Characteristics

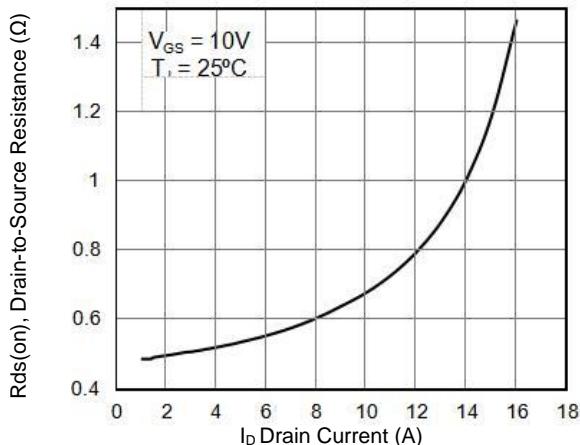


Figure 3. On-Resistance versus Drain Current

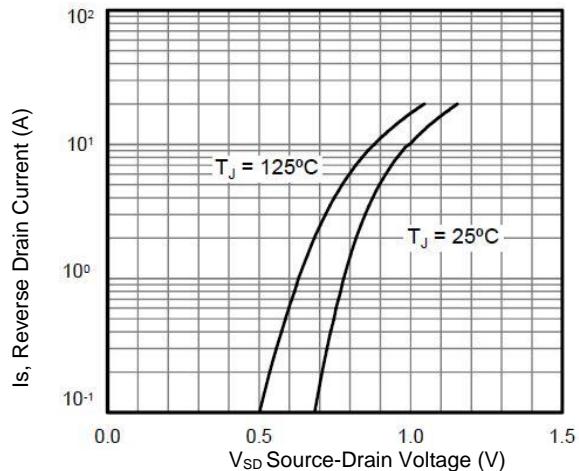


Figure 4. Diode forward voltage versus Current

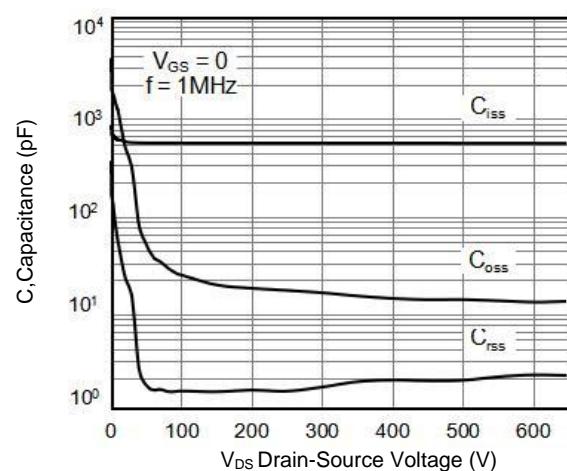


Figure 5. Typical Capacitance versus V_{DS}

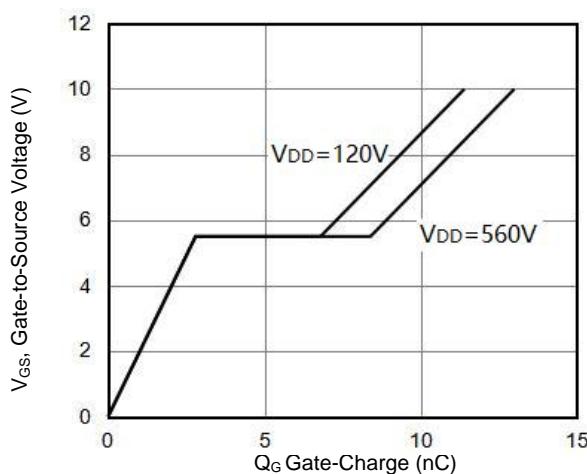


Figure 6. Typical Gate Charge versus V_{GS}

5. Electrical Characteristics (cont.)

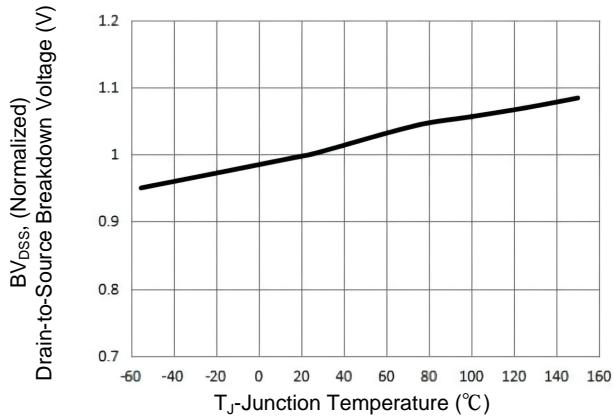


Figure 7. BV_{DSS} Variation with Temperature

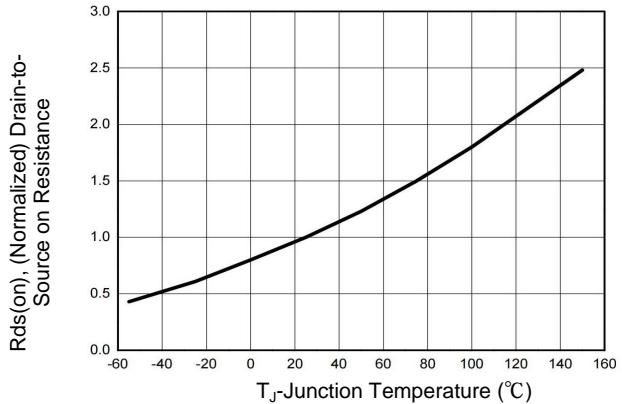


Figure 8. On-Resistance Variation with Temperature

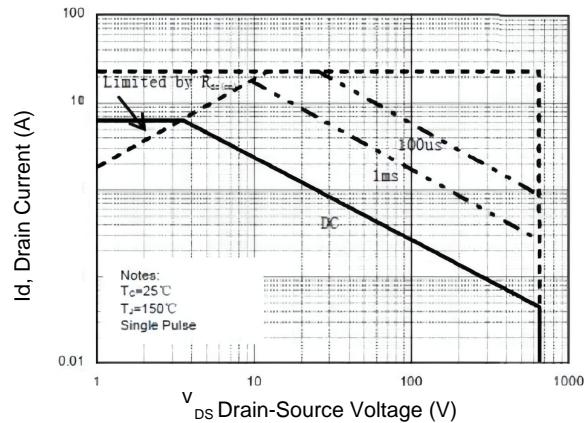


Figure 9. Maximum Safe Operating Area

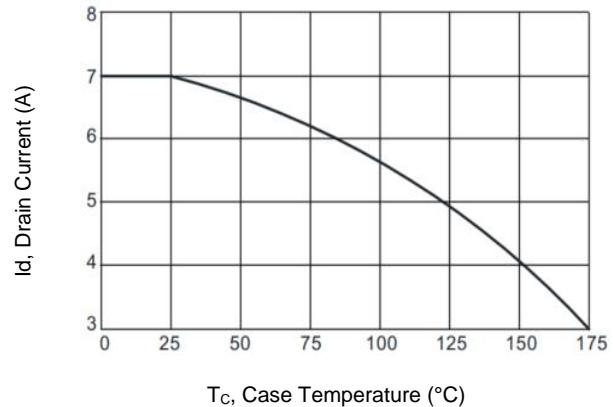
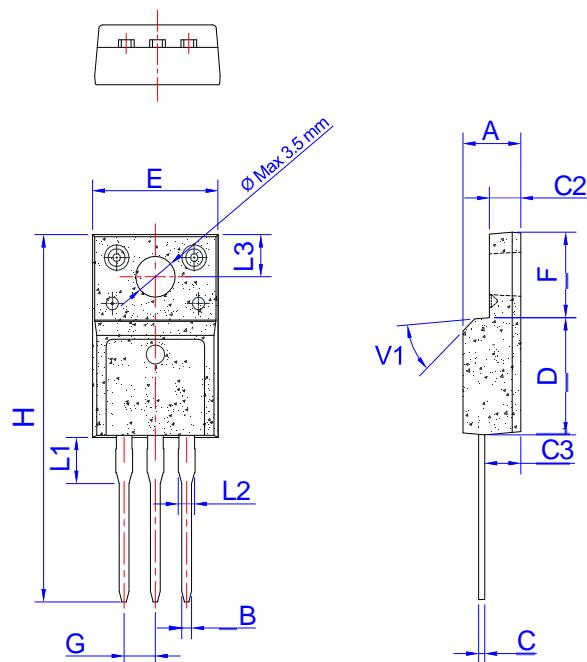


Figure 10. Maximum Continuous Drain Current versus Case Temperature

6. Package Mechanical Data

- TO-220F Package



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX
A	4.50		4.90
B	0.74	0.80	0.83
C	0.47		0.65
C2	2.45		2.75
C3	2.60		3.00
D	8.80		9.30
E	9.80		10.4
F	6.40		6.80
G		2.54	
H	28.0		29.8
L1		3.63	
L2	1.14		1.70
L3		3.30	
V1		45°	